

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI VHB1-28T** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.4 A
V_{CB0}	55 V
V_{CEO}	30 V
V_{EBO}	3.5 V
P_{DISS}	5 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	35 °C/W

PACKAGE STYLE TO-39

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.200 / 5.080	
B	.029 / 0.740	.045 / 1.140
C	.028 / 0.720	.034 / 0.860
D	.335 / 8.510	.370 / 9.370
E	.305 / 7.750	.335 / 8.500
F	.240 / 6.100	.260 / 6.600
G	.500 / 12.700	
H	.016 / 0.407	.020 / 0.508

ORDER CODE: ASI10720

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 5.0 mA	30			V
BV_{CER}	I _C = 5.0 mA R _{BE} = 10 Ω	55			V
BV_{CB0}	I _C = 0.1 mA	55			V
BV_{EBO}	I _E = 0.1 mA	3.5			V
I_{CEX}	V _C = 55 V V _{BE} = -1.5 V			100	μA
I_{CEO}	V _E = 28 V			20	μA
V_{CE}^(S)	I _C = 100 mA I _B = 20 mA			1.0	V
h_{FE}	V _{CE} = 5.0 V I _C = 50 mA I _C = 360 mA	10 5.0		200	---
C_{OB}	V _{CB} = 28 V f = 1.0 MHz			3.0	pF
P_G η	V _{CE} = 28 V P _{OUT} = 1.0 W f = 175 MHz	13	60		dB %